

SILICON BIDIRECTIONAL THYRISTORS

MAC212(A) SERIES

High-reliability discrete products and engineering services since 1977

FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak repetitive off-state voltage ⁽¹⁾			
(T _J = -40 to +125°C, ½ sine wave 50 to 60 Hz, gate open)			
MAC212-4, MAC212A-4	V _{DRM}	200	Volts
MAC212-6, MAC212A-6	V DRM	400	VOILS
MAC212-8, MAC212A-8		600	
MAC212-10, MAC212A-10		800	
RMS on-state current (full sine wave, 50 to 60Hz, $T_c = 85$ °C)	I _{T(RMS)}	12	Amps
Peak non-repetitive surge current			Amns
(1 cycle, 60 Hz, T_c = 85°C, preceded and followed by rated current)	I _{TSM}	100	Amps
Circuit fusing considerations (t = 8.3ms)	l ² t	40	A ² s
Peak gate power	D		Watts
$(T_c = 85^{\circ}C, \text{ pulse width} = 10\mu\text{s})$	P _{GM}	20	
Average gate power			Watts
$(T_c = 85^{\circ}C, t = 8.3 \text{ms})$	$P_{G(AV)}$	0.35	
Peak gate current		2.0	A
$(T_c = 85^{\circ}C, \text{ pulse width} = 10\mu\text{s})$	I _{GM}	2.0	Amps
Operating junction temperature range	T,	-40 to +125	°C
Storage temperature range	T _{stg}	-40 to +150	°C

Note 1: V_{DRM} for all types can be applied on a continuous basis. Blocking voltage shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Maximum	Unit
Thermal resistance, junction to case	R _{OJC}	2.1	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур.	Max	Unit
Peak blocking current (either direction)					
$(V_D = Rated V_{DRM} @ T_J = 25^{\circ}C)$	I _{DRM}	-	-	10	μΑ
$(V_D = Rated V_{DRM} @ T_J = 125^{\circ}C)$		-	-	2	mA
Peak on-state voltage (either direction)					\
(I_{TM} = 17A peak, pulse width = 1 to 2 ms, duty cycle \leq 2%)	V_{TM}	-	1.3	1.75	Volts
Gate trigger current (continuous dc)					
(main terminal voltage = 12V, $R_L = 100\Omega$)					
MT2(+),G(+)		-	12	50	^
MT2(+),G(-)	I _{GT}	-	12	50	mA
MT2(-),G(-)		-	20	50	
MT2(-),G(+) "A" suffix only		-	35	75	



High-reliability discrete products and engineering services since 1977

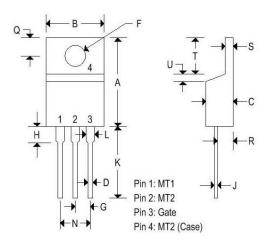
MAC212(A) SERIES

SILICON BIDIRECTIONAL THYRISTORS

Gate trigger voltage (continuous dc)					
(main terminal voltage = 12V, $R_L = 100\Omega$)					
MT2(+),G(+)		-	0.9	2	
MT2(+),G(-)		-	0.9	2	
MT2(-),G(-)	V_{GT}	-	1.1	2	Volts
MT2(-),G(+) "A" suffix only		-	1.4	2.5	
(main terminal voltage= Rated V_{DRM} , $R_L = 10k\Omega$, $T_J = 125$ °C)					
MT2(+), G(+); MT2(-), G(-); MT2(+), G(-)		0.2	-	-	
MT2(-), G(+) "A" suffix only		0.2	-	-	
Holding current (either direction)	I _H				mA
(main terminal voltage= 12V, gate open, initiating current = 500mA)		-	6	50	
Turn on time	t _{gt}				μs
$(V_D = Rated V_{DRM}, I_{TM} = 17A, I_{GT} = 120mA, rise time = 0.1 \mu s, pulse width = 2 \mu s)$		-	1.5	-	
Critical rate of rise of commutation voltage	dv/dt(c)	-	5	-	V/µs
$(V_D = Rated V_{DRM}, I_{TM} = 17A, commutating di/dt = 6.1A/ms, gate unenergized,$					
$T_c = 85$ °C)					
Critical rate of rise of off-state voltage	dv/dt				V/µs
$(V_D = Rated V_{DRM}, exponential voltage rise, gate open, T_C = 85°C)$		-	100	-	

MECHANICAL CHARACTERISTICS

Case	TO-220AB
Marking	Alpha-numeric
Pin out	See below



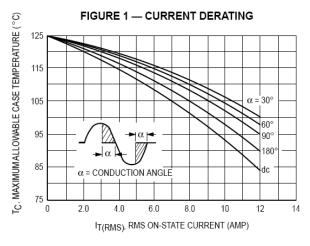
	TO-220AB				
	Inches		Millimeters		
	Min	Max	Min	Max	
Α	0.575	0.620	14.600	15.750	
В	0.380	0.405	9.650	10.290	
С	0.160	0.190	4.060	4.820	
D	0.025	0.035	0.640	0.890	
F	0.142	0.147	3.610	3.730	
G	0.095	0.105	2.410	2.670	
Н	0.110	0.155	2.790	3.930	
J	0.014	0.022	0.360	0.560	
K	0.500	0.562	12.700	14.270	
L	0.045	0.055	1.140	1.390	
N	0.190	0.210	4.830	5.330	
Q	0.100	0.120	2.540	3.040	
R	0.080	0.110	2.040	2.790	
S	0.045	0.055	1.140	1.390	
T	0.235	0.255	5.970	6.480	
U	12	0.050	197	1.270	
٧	0.045		1.140		
Z	2	0.080	121	2.030	



High-reliability discrete products and engineering services since 1977

MAC212(A) SERIES

SILICON BIDIRECTIONAL THYRISTORS



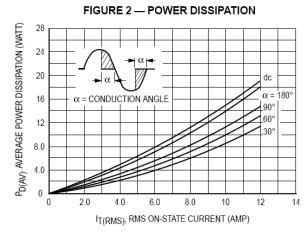


FIGURE 3 — MAXIMUM ON-STATE CHARACTERISTICS

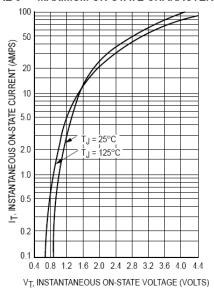


FIGURE 4 — MAXIMUM NON-REPETITIVE SURGE CURRENT

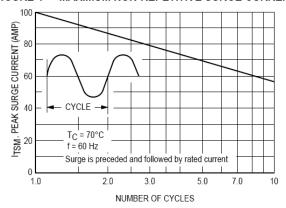
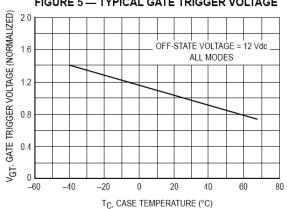


FIGURE 5 — TYPICAL GATE TRIGGER VOLTAGE





High-reliability discrete products and engineering services since 1977

MAC212(A) SERIES

SILICON BIDIRECTIONAL THYRISTORS

